

QUAD MONOLITHIC, SPST CMOS/DMOS ANALOG SWITCHES

FEATURES

- High OFF Isolation68 dB @ 10 MHz
- Low Insertion Loss-1 dB @ 100 MHz
- Low Channel-to-Channel
Cross Talk-80 dB @ 10 MHz
- CMOS-Compatible Inputs
- Low OFF Leakage
- Industry Standard Pinout (CDG308/CDG309)

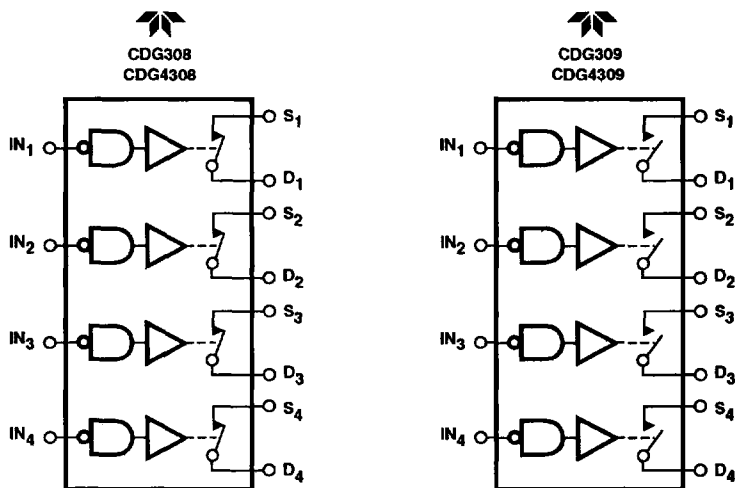
APPLICATIONS

- Glitch-Free Analog Switching
- RF and Video
- Track-and-Hold
- Sample-and-Hold

GENERAL DESCRIPTION

Teledyne Components' CMOS/DMOS analog switches feature high-speed, low-power CMOS input logic and level translation circuitry, and high-speed, low-capacitance, lateral DMOS switches. CMOS and lateral DMOS circuitry are fabricated together on a single silicon chip. The CDG4308 and CDG4309 use the same die as CDG308 and CDG309; the extra isolating pin between switch input and output increases isolation by 6 dB.

FUNCTIONAL BLOCK DIAGRAMS

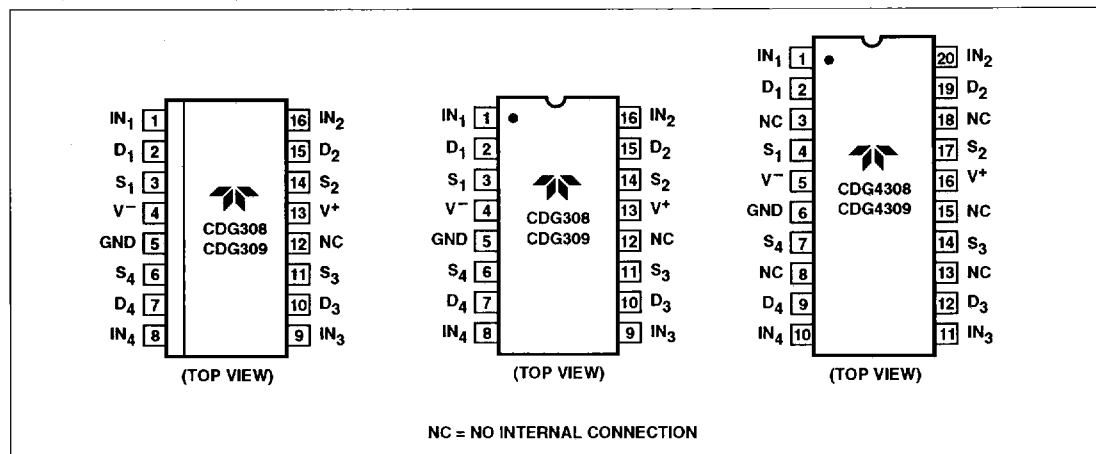


- NOTES: 1. Four SPST switches per package.
2. Switches shown in logic "1" position.
3. CDG308/CDG4308: Logic "0" = OFF; Logic "1" = ON
CDG309/CDG4309: Logic "0" = ON; Logic "1" = OFF

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CDG308 CDG4308
CDG309 CDG4309

PIN CONFIGURATIONS



ORDERING INFORMATION

Part No.	Package	Operating Temperature Range
CDG308COE	16-Pin SO	0°C to +70°C
CDG308CPE	16-Pin Plastic DIP	0°C to +70°C
CDG308EJE	16-Pin CerDIP	-40°C to +85°C
CDG308EOE	16-Pin SO	-40°C to +85°C
CDG308EPE	16-Pin Plastic DIP	-40°C to +85°C
CDG308MJE	16-Pin CerDIP	-55°C to +125°C
CDG309COE	16-Pin SO	0°C to +70°C
CDG309CPE	16-Pin Plastic DIP	0°C to +70°C
CDG309EJE	16-Pin CerDIP	-40°C to +85°C
CDG309EOE	16-Pin SO	-40°C to +85°C
CDG309EPE	16-Pin Plastic DIP	-40°C to +85°C
CDG309MJE	16-Pin CerDIP	-55°C to +125°C
CDG4308CPP	20-Pin Plastic DIP	0°C to +70°C
CDG4308EPP	20-Pin Plastic DIP	-40°C to +85°C
CDG4309CPP	20-Pin Plastic DIP	0°C to +70°C
CDG4309EPP	20-Pin Plastic DIP	-40°C to +85°C

ABSOLUTE MAXIMUM RATINGS

Negative Supply Voltage	-20V
Positive Supply Voltage	+20V
Control Input Voltage Range	V ⁺ +0.3V, V ⁻ -0.3V
Continuous Current, Any Pin Except S or D	20 mA
Continuous Current, S or D	30 mA
Peak Pulsed Current, S or D,	
80 μs, 1%, Duty Cycle	180 mA
Junction Temperature Range	-55°C to +125°C
Storage Temperature Range	-65°C to +150°C
Power Dissipation	500 mW

NOTE: All devices contain diodes to protect inputs against damage due to high-static voltages or electric fields. However, it is advised precautions be taken not to exceed the maximum recommended input voltages. All unused inputs must be connected to an appropriate logic voltage level (V_{DD} or GND). Static-sensitive device. Unused devices must be stored in conductive material. Protect devices from static discharge and static fields. Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to Absolute Maximum Rating Conditions for extended periods may affect device reliability.

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CDG308 **CDG4308**
CDG309 **CDG4309**

RECOMMENDED OPERATING CONDITIONS

Negative Supply Voltage -8V to -15V
Positive Supply Voltage +8V to +15V
Control Input Voltage Range 0V to +5V
Analog Switch Voltage Range ±10V
Operating Temperature Range
 C Suffix 0°C to +70°C
 E Suffix -40°C to +85°C
 M Suffix -55°C to +125°C

ELECTRICAL CHARACTERISTICS: $T_A = +25^\circ\text{C}$, $V^- = -15\text{V}$, $V^+ = +15\text{V}$ per channel, unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static						
V_{ANALOG}	Analog Signal Range		-10	—	+10	V
$r_{\text{DS(ON)}}$	Switch ON Resistance	$V_S = -10\text{V}$ $V_S = +2\text{V}$ $V_S = +10\text{V}$	— — —	40 45 100	80 80 160	Ω Ω Ω
V_{IH}	High Level Input Voltage		4.5	3.4	—	V
V_{IL}	Low Level Input Voltage		—	—	1	V
I_{IN}	Logic Input Leakage Current	$V_{\text{IN}} = +5\text{V}$ $V_{\text{IN}} = +15\text{V}$	— —	0.01 0.02	0.1 0.1	μA μA
$I_{\text{D(OFF)}}$	Switch OFF Leakage Current	$V_D = +10\text{V}$, $V_S = -10\text{V}$ $V_{\text{IN}} = +5\text{V}$ (CDG309/CDG4309) $V_{\text{IN}} = +1\text{V}$ (CDG308/CDG4308)	—	0.2	5	nA
$I_{\text{S(OFF)}}$	Switch OFF Leakage Current	$V_S = +10\text{V}$, $V_D = -10\text{V}$ $V_{\text{IN}} = +5\text{V}$ (CDG309/CDG4309) $V_{\text{IN}} = +1\text{V}$ (CDG308/CDG4308)	—	0.4	5	nA
I^-	Negative Supply Quiescent Current	$V_{\text{IN}} = +5\text{V}$ (CDG309/CDG4309) $V_{\text{IN}} = +1\text{V}$ (CDG308/CDG4308)	—	-0.1	-0.5	μA
I^+	Positive Supply Quiescent Current	$V_{\text{IN}} = +5\text{V}$ (CDG309/CDG4309) $V_{\text{IN}} = +1\text{V}$ (CDG308/CDG4308)	—	0.1	0.5	μA
Dynamic						
t_{ON}	Switch Turn-On Time	$V_{\text{IN}} = +1\text{V}$ (CDG308/CDG4308) $V_{\text{IN}} = +5\text{V}$ (CDG309/CDG4309)	—	140 80	250 220	ns
t_{OFF}	Switch Turn-Off Time	$V_{\text{IN}} = +1\text{V}$ (CDG308/CDG4308) $V_{\text{IN}} = +5\text{V}$ (CDG309/CDG4309)	—	80	220	ns
OIRR	Off Isolation Rejection Ratio	$f = 10\text{ MHz}$, $R_L = 50\Omega$ (CDG308/CDG309) $f = 10\text{ MHz}$, $R_L = 50\Omega$ (CDG4308/CDG4309)	60 66	62 68	— —	dB dB
C_{CRR}	Cross-Coupling Rejection Ratio	$f = 10\text{ MHz}$, $R_L = 50\Omega$	—	80	—	dB
C_D	Drain-Node Capacitance	$V_D = V_S = 0$, $f = 1\text{ MHz}$ $V_{\text{IN}} = +1\text{V}$ (CDG308/CDG4308) $V_{\text{IN}} = +5\text{V}$ (CDG309/CDG4309)	—	0.3	—	pF
C_S	Source-Node Capacitance	$V_D = V_S = 0$, $f = 1\text{ MHz}$ $V_S = 0$, $f = 1\text{ MHz}$, $V_{\text{IN}} = 0\text{V}$ $V_{\text{IN}} = +5\text{V}$ (CDG309/CDG4309)	—	3	—	pF

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ELECTRICAL CHARACTERISTICS: $V^- = -15V$, $V^+ = +15V$ per channel, unless otherwise noted.
Limits at Temperature Extremes

Symbol	Parameter	Test Conditions	Maximum @ T _A =					Unit
			−55°C	−40°C	+70°C	+85°C	+125°C	
Static								
V _{ANALOG}	Analog Signal Range		±10	±10	±10	±10	±10	V
r _{DS(ON)}	Switch ON Resistance	V _S = +2V, V _S = −10V V _S = +10V	80 160	80 160	120 240	120 240	150 300	Ω Ω
I _{IN}	Logic Input Leakage Current	V _{IN} = +5V V _{IN} = +15V	0.1 0.1	0.1 0.1	1 2	1 2	10 20	μA μA
I _{D(OFF)}	Switch OFF Leakage Current	V _D = +10V, V _S = −10V	5	5	100	100	1000	nA
I _(OFF)	Switch OFF Leakage Current	V _S = +10V, V _D = −10V	5	5	100	100	1000	nA
I [−]	Negative Supply Quiescent Current		−0.5	−0.5	−20	−20	−100	μA
I ⁺	Positive Supply Quiescent Current		0.5	0.5	20	20	100	μA

SWITCH CONTACTS

Switches are bidirectional (analog input can be to source or drain). However, for optimum performance in video applications, connect input to source and output to drain. (See Figure 1.)

POWER SUPPLY DECOUPLING CIRCUIT

By inserting 1 k Ω resistors in series with V^+ and V^- power supply lines, and decoupling both pins at the device socket, it is possible to improve video switch power supply rejection ratios by 50 dB at frequencies of 20 MHz and higher. (See Figure 2.)

APPLICATIONS

Very Low Distortion Circuit for Low Frequency/Large Signal Applications

The circuit shown in Figure 3 provides very low distortion (<0.1%) and high off isolation (>90 dB) at signal levels equal to the supply voltage. The signal passes through a "T" switch configuration and at the same time modulates the power supply. This modulation maintains a constant ON resistance, $r_{DS(ON)}$, which in turn reduces distortion. R5 is for bypassing the power supply and has a typical value of 1 k Ω ; R4 should be a value that can be accommodated by the signal source as load; R3 is only necessary at loads lower

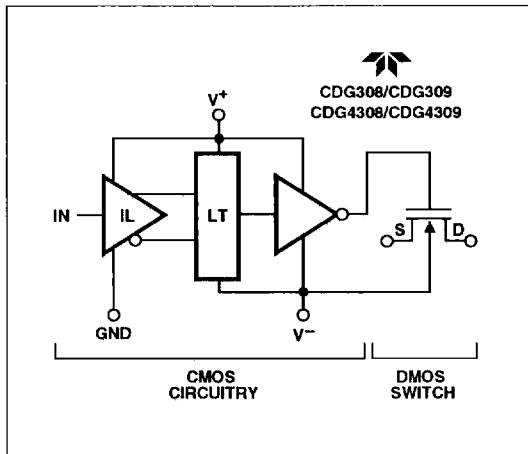


Figure 1 Functional Diagram (1 of 4 Channels)

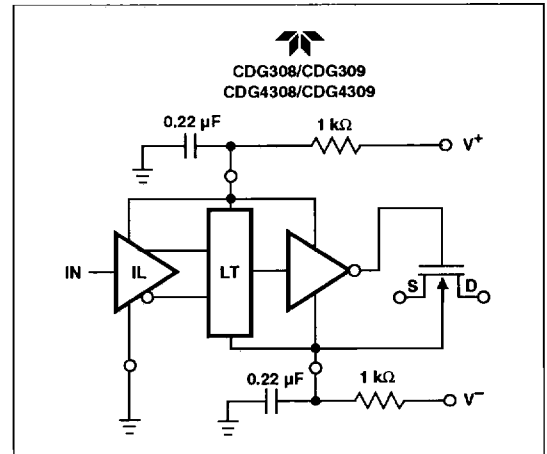


Figure 2 Power Supply Decoupling Circuit

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than 100Ω and should be selected during initial circuit design; C_1 has to be large enough for the lowest signal to pass and C_2 will have to bypass all signals. R_1 and R_2 set up the logic "1" level for the control input and should be set to 5V.

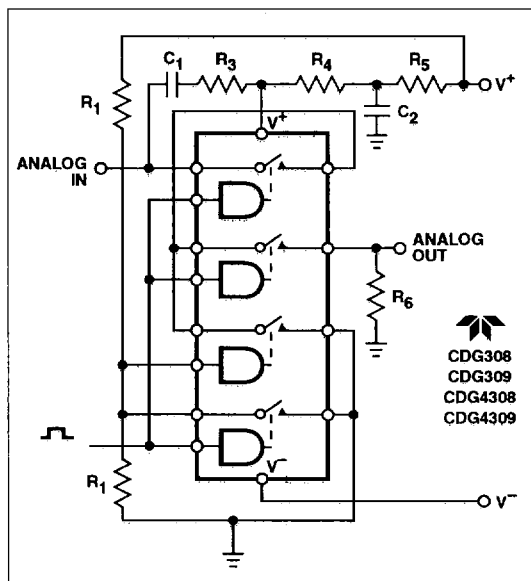


Figure 3 Low Distortion, Rail-to-Rail Analog Switch

Logic Inverter

The circuit shown in Figure 4 provides logic inversion with two resistors and one switch. It does not require additional logic parts. The resistors divide the supply voltage to a 5V level when high, and are switched to a low level via the switch. This configuration allows a single-pole, single-throw switch to be changed into a single-pole, double-throw switch.

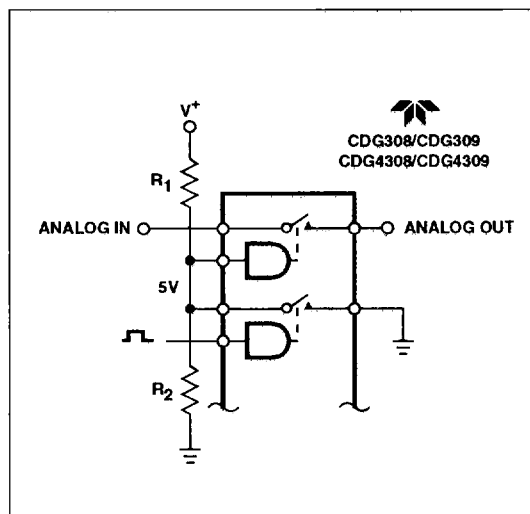
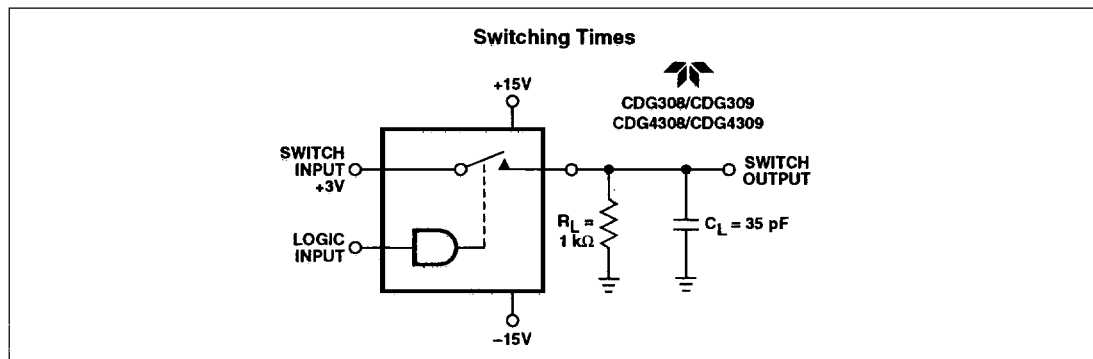


Figure 4 Logic Inverter

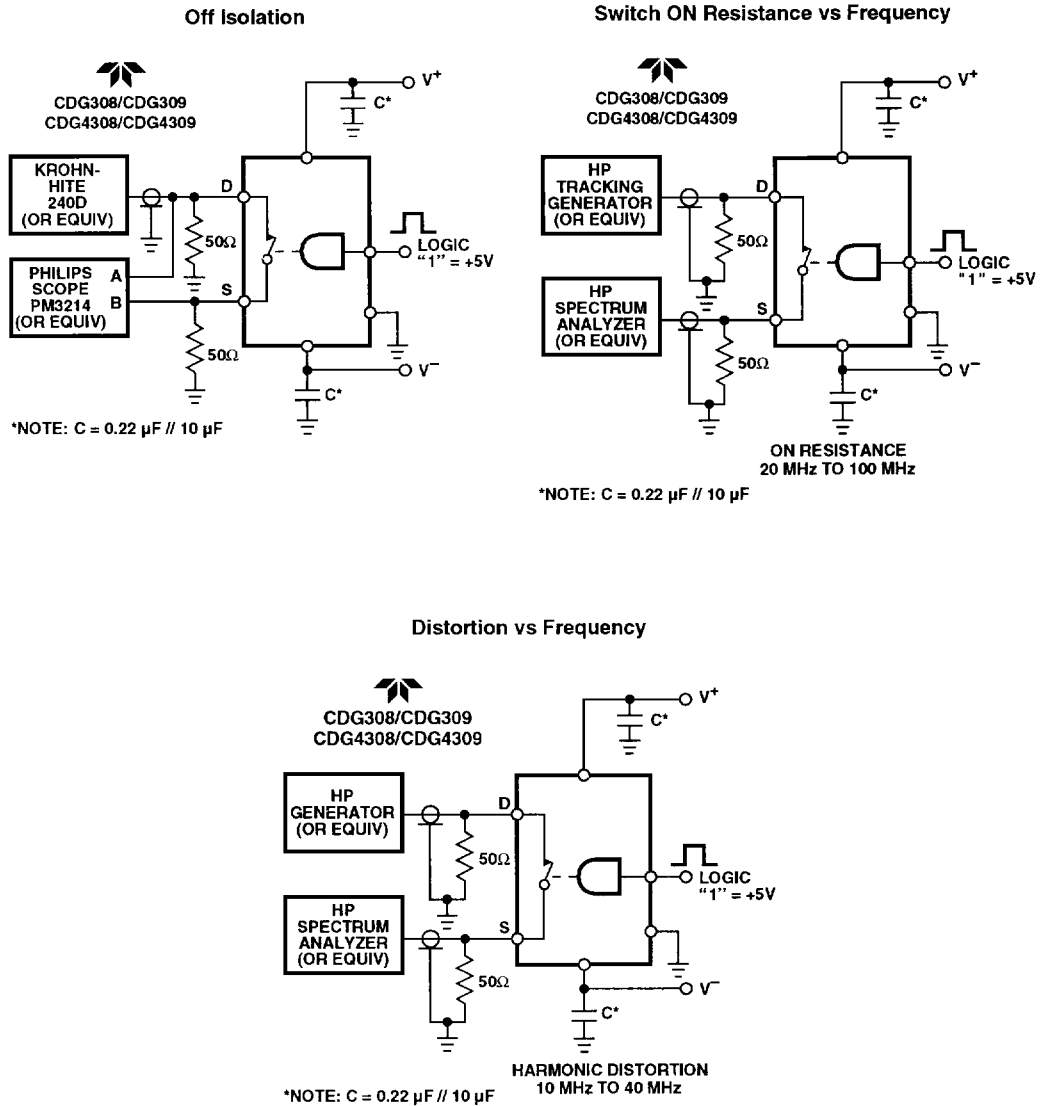
TEST CIRCUITS



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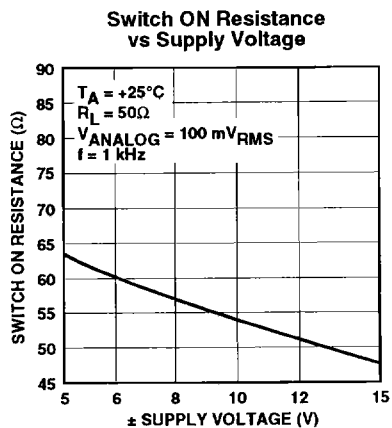
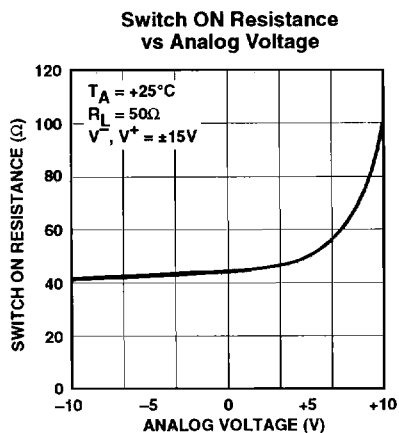
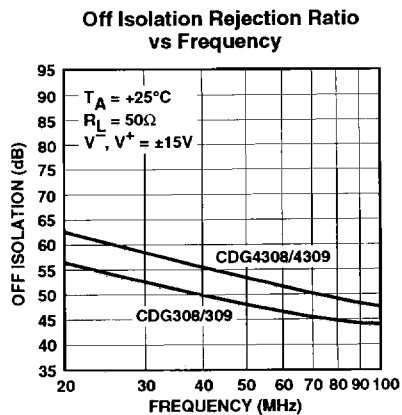
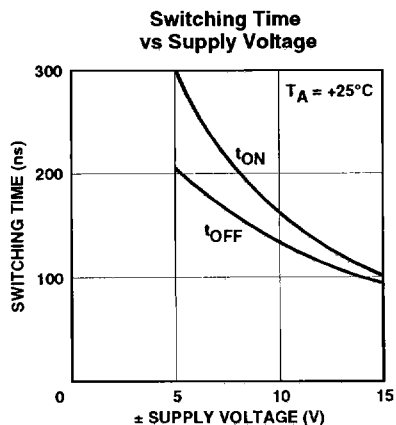
TEST CIRCUITS (Cont.)



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TYPICAL PERFORMANCE CHARACTERISTICS



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CDG309 CDG4309

TYPICAL PERFORMANCE CHARACTERISTICS (Cont.)

